











WL1801MOD, WL1805MOD, WL1831MOD, WL1835MOD

SWRS152L-JULY 2013-REVISED DECEMBER 2015

WL18xxMOD WiLink[™] 8 Single-Band Combo Module – Wi-Fi[®], *Bluetooth*[®], and *Bluetooth* Low Energy (LE)

1 Device Overview

1.1 Features

General

- Integrates RF, Power Amplifiers (PAs), Clock, RF Switches, Filters, Passives, and Power Management
- Quick Hardware Design With TI Module Collateral and Reference Designs
- Operating Temperature: -20°C to 70°C
- Small Form Factor: 13.3 x 13.4 x 2 mm
- 100-Pin MOC Package
- FCC, IC, ETSI/CE, and TELEC Certified

Wi-Fi

- WLAN Baseband Processor and RF Transceiver Support of IEEE Std 802.11a, 802.11b, 802.11g, and 802.11n
- 20- and 40-MHz SISO and 20-MHz 2 x 2 MIMO at 2.4 GHz for High Throughput: 80 Mbps (TCP), 100 Mbps (UDP)
- 2.4-GHz MRC Support for Extended Range
- Fully Calibrated: Production Calibration Not Required
- 4-Bit SDIO Host Interface Support
- Wi-Fi Direct Concurrent Operation (Multichannel, Multirole)

1.2 Applications

- Internet of Things (IoT)
- Multimedia
- Home Electronics
- Home Appliances and White Goods

Bluetooth and Bluetooth LE (WL183xMOD Only)

- Bluetooth 4.1 Compliance and CSA2 Support
- Host Controller Interface (HCI) Transport for Bluetooth Over UART
- Dedicated Audio Processor Support of SBC Encoding + A2DP
- Dual-Mode Bluetooth and Bluetooth LE
- TI's Bluetooth- and Bluetooth LE-Certified Stack

Key Benefits

- Reduces Design Overhead
- Differentiated Use-Cases by Configuring WiLink 8 Simultaneously in Two Roles (STA and AP) to Connect Directly With Other Wi-Fi Devices on Different RF Channel (Wi-Fi Networks)
- Best-in-Class Wi-Fi With High-Performance Audio and Video Streaming Reference Applications With Up to 1.4X the Range Versus One Antenna
- Different Provisioning Methods for In-Home Devices Connectivity to Wi-Fi in One Step
- Lowest Wi-Fi Power Consumption in Connected Idle (< 800 μA)
- Configurable Wake on WLAN Filters to Only Wake up the System
- Wi-Fi-Bluetooth Single Antenna Coexistence
- · Industrial and Home Automation
- Smart Gateway and Metering
- Video Conferencing
- · Video Camera and Security





1.3 Description

The certified WiLink 8 module from TI offers high throughput and extended range along with Wi-Fi and *Bluetooth* coexistence (WL1835MOD only) in a power-optimized design. The WL18x5MOD device is a 2.4-GHz module, two antenna solution. The device is FCC, IC, ETSI/CE, and TELEC certified for AP and client. TI offers drivers for high-level operating systems such as Linux[®] and Android[™]. Additional drivers, such as WinCE and RTOS, which includes QNX, Nucleus, ThreadX, and FreeRTOS, are supported through third parties.

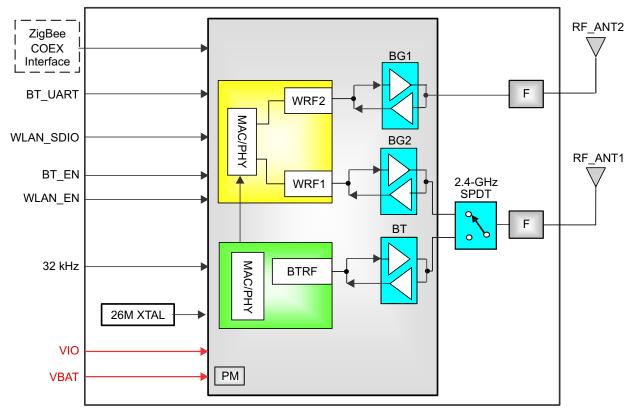
Device Information⁽¹⁾

ORDER NUMBER	PACKAGE	BODY SIZE
WL1801MOD	MOC (100)	13.3 mm × 13.4 mm × 2 mm
WL1805MOD	MOC (100)	13.3 mm × 13.4 mm × 2 mm
WL1831MOD	MOC (100)	13.3 mm × 13.4 mm × 2 mm
WL1835MOD	MOC (100)	13.3 mm × 13.4 mm × 2 mm

⁽¹⁾ For more information, see Section 9, Mechanical Packaging and Orderable Information.

1.4 Functional Block Diagram

Figure 1-1 shows a functional block diagram of the WL1835MOD variant.



NOTE: Dashed lines indicate optional configurations and are not applied by default.

Figure 1-1. WL1835MOD Functional Block Diagram



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2 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision K (November 2014) to Revision L Page Changed Features section Changed Section 1.3, Description. Changed description for pin 14 (WL_IRQ_1V8) in Table 4-1 8 Changed parameter heading from "2G4_ANT2_W + 2G4_ANT1_WB Pins" in Section 5.8, WLAN Performance: Added note on maximum transmitter power degradation and changed note on regulatory constraints in Added note 1 in Section 5.10, Bluetooth Performance: BR, EDR Receiver Characteristics—In-Band Signals 15 Changed note 3 from "Assumes VBAT ADC measurement accuracy of 5%" in Section 5.11, Bluetooth Transmitter, BR..... Changed BR RF output power from 12.7 dBm typical in Section 5.11, Bluetooth Performance: Transmitter, BR ... 16

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Added note 1 in Section 5.11, Bluetooth Transmitter, BR	16
Changed note 3 from "Assumes VBAT ADC measurement accuracy of 5%" in Section 5.12, Bluetooth	
Transmitter, EDR	16
Added note 1 in Section 5.15, Bluetooth LE Performance: Receiver Characteristics – In-Band Signals	<u>17</u>
Changed note 3 from "Assumes VBAT ADC measurement accuracy of 5%"	18
Changed Bluetooth LE RF transmitter output power from 10.0 dBm typical (VBAT ≥ 3V) and 7.2 dBM (VBAT ≤	
3V) in Section 5.16, Bluetooth LE Performance: Transmitter Characteristics	18
Added note 1 through note 3 in Section 5.16, Bluetooth LE Performance: Transmitter Characteristics	18
Deleted note: "To reduce the maximum BLE power, use a VS command. The optional extra margin is offered to	
compensate for design losses, such as trace and filter losses, and to achieve the maximum allowed output	
power at system level." in Section 5.16, Bluetooth LE Performance: Transmitter Characteristics	
Added note 1 in Section 5.17, Bluetooth LE Performance: Modulation Characteristics	
Changed reference design from WL1835MODB in Section 7.1.1, Typical Application – WL1835MODGB	
Changed Figure 7-1	31
Added Section 9.2, Tape and Reel Information	40
	Changed note 3 from "Assumes VBAT ADC measurement accuracy of 5%" in Section 5.12, Bluetooth Transmitter, EDR



3 Device Comparison

The TI WiLink 8 module offers four footprint-compatible 2.4-GHz variants providing stand-alone Wi-Fi and *Bluetooth* combo connectivity. Table 3-1 compares the features of the module variants.

Table 3-1. TI WiLink 8 Module Variants

DEVICE	WLAN 2.4-GHZ SISO ⁽¹⁾	WLAN 2.4-GHZ MIMO ⁽¹⁾	WLAN 2.4-GHZ MRC ⁽¹⁾	BLUETOOTH
WL1835MOD	√	\checkmark	√	√
WL1831MOD	√			√
WL1805MOD	√	√	√	
WL1801MOD	√			

⁽¹⁾ SISO: single input, single output; MIMO: multiple input, multiple output; MRC: maximum ratio combining, supported at 802.11 g/n.

4 Terminal Configuration and Functions

Figure 4-1 shows the pin assignments for the 100-pin MOC package.

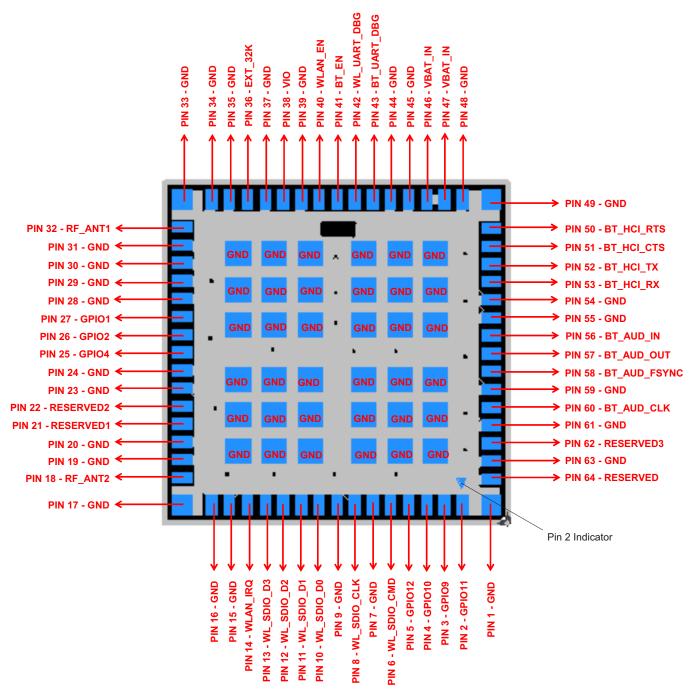
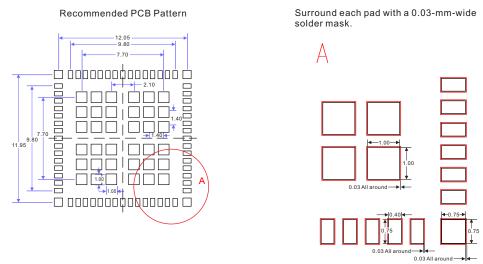


Figure 4-1. 100-Pin MOC Package (Bottom View)



Figure 4-2 shows the recommended PCB pattern of the 100-pin MOC package.



- NOTE: 1. Module size: 13.4 mm x 13.3 mm
 - 2. Signal pad size: 0.75 mm × 0.40 mm
 - 3. 4 x corner ground size: 0.75 mm x 0.75 mm
 - 4. Central ground pin size: 1.00 mm x 1.00 mm
 - 5. Pitch: 0.7 mm

Figure 4-2. Recommended PCB Pattern of 100-Pin MOC Package

Figure 4-3 shows the recommended stencil outline of the 100-pin MOC package.

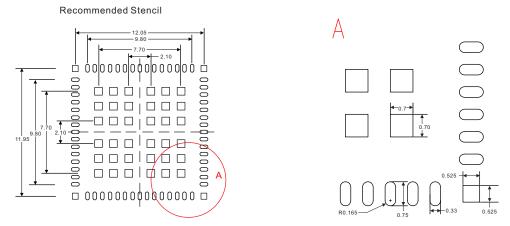


Figure 4-3. Recommended Stencil Outline of 100-Pin MOC Package



4.1 Pin Description

Table 4-1 describes the module pins.

Table 4-1. Pin Description

PIN NAME	PIN	TYPE/	SHUTDOWN	AFTER	VOLTAGE	C	ONNEC	TIVITY(2)	DESCRIPTION
		DIR	STATE	POWER UP(1)	LEVEL	1801	1805	1831	1835	
Clocks and Reset Sig	gnals									
WL_SDIO_CLK	8	I	Hi-Z	Hi-Z	1.8 V	V	V	V	V	WLAN SDIO clock. Must be driven by the host.
EXT_32K	36	ANA			-	V	V	V	V	Input sleep clock: 32.768 kHz
WLAN_EN	40	1	PD	PD	1.8 V	V	V	V	V	Mode setting: high = enable
BT_EN	41	I	PD	PD	1.8 V	х	х	٧	V	Mode setting: high = enable
Power-Management S	Signals									
VIO_IN	38	POW	PD	PD	1.8 V	V	V	V	V	Connect to 1.8-V external VIO
VBAT_IN	46	POW			VBAT	V	V	V	V	Power supply input, 2.9 to 4.8 V
VBAT_IN	47	POW			VBAT	V	٧	V	V	Power supply input, 2.9 to 4.8 V
TI Reserved										
GPIO11	2	I/O	PD	PD	1.8 V	V	V	V	V	Reserved for future use. NC if not used.
GPIO9	3	I/O	PD	PD	1.8 V	V	V	V	V	Reserved for future use. NC if not used.
GPIO10	4	I/O	PU	PU	1.8 V	V	V	V	V	Reserved for future use. NC if not used.
GPIO12	5	I/O	PU	PU	1.8 V	V	V	V	V	Reserved for future use. NC if not used.
RESERVED1	21	1	PD	PD	1.8 V	Х	Х	Х	Х	Reserved for future use. NC if not used.
RESERVED2	22	I	PD	PD	1.8 V	Х	Х	Х	Х	Reserved for future use. NC if not used.
GPIO4	25	I/O	PD	PD	1.8 V	V	V	V	V	Reserved for future use. NC if not used.
RESERVED3	62	0	PD	PD	1.8 V	х	х	х	Х	Reserved for future use. NC if not used.
WLAN Functional Blo	ock: Int	Signals	,					ı		
WL_SDIO_CMD_1V 8	6	I/O	Hi-Z	Hi-Z	1.8 V	V	V	V	V	WLAN SDIO command(3)
WL_SDIO_D0_1V8	10	I/O	Hi-Z	Hi-Z	1.8 V	٧	٧	٧	V	WLAN SDIO data bit 0(3)
WL_SDIO_D1_1V8	11	I/O	Hi-Z	Hi-Z	1.8 V	V	V	٧	V	WLAN SDIO data bit 1(3)
WL_SDIO_D2_1V8	12	Ю	Hi-Z	Hi-Z	1.8 V	V	V	V	V	WLAN SDIO data bit 2(3)
WL_SDIO_D3_1V8	13	I/O	Hi-Z	PU	1.8 V	V	V	V	V	WLAN SDIO data bit 3. Changes state to PU at WL_EN or BT_EN assertion for card detects. Later disabled by software during initialization.(3)



Table 4-1. Pin Description (continued)

PIN NAME	PIN	TYPE/	SHUTDOWN	AFTER	VOLTAGE	C	ONNEC	TIVITY(2)	DESCRIPTION
		DIR	STATE	POWER UP(1)	LEVEL	1801	1805	1831	1835	
WL_IRQ_1V8	14	0	PD	0	1.8 V	V	V	V	V	WLAN SDIO out-of- band interrupt line. Set to rising edge (active high) by default. (To extract the debug option WL_RS232_TX/RX interface out, pull up the IRQ line at power up before applying enable.)
RF_ANT2	18	ANA			-	х	٧	x	V	2.4-GHz ANT2 TX, RX; 2.4-GHz secondary antenna MRC/MIMO only.
GPIO2	26	I/O	PD	PD	1.8 V	V	V	٧	V	WL_RS232_RX (when WLAN_IRQ = 1 at power up)
GPIO1	27	I/O	PD	PD	1.8 V	V	V	V	V	WL_RS232_TX (when WLAN_IRQ = 1 at power up)
RF_ANT1	32	ANA			-	V	V	V	V	2.4-GHz WLAN main antenna SISO, Bluetooth
WL_UART_DBG	42	0	PU	PU	1.8 V	V	V	٧	V	Option: WLAN logger
Bluetooth Functional	Block:	Int Signa	ls							
BT_UART_DBG	43	0	PU	PU	1.8 V	Х	х	٧	V	Option: Bluetooth logger
BT_HCI_RTS_1V8	50	0	PU	PU	1.8 V	х	х	٧	V	UART RTS to host. NC if not used.
BT_HCI_CTS_1V8	51	I	PU	PU	1.8 V	х	х	٧	V	UART CTS from host. NC if not used.
BT_HCI_TX_1V8	52	0	PU	PU	1.8 V	х	х	٧	V	UART TX to host. NC if not used.
BT_HCI_RX_1V8	53	I	PU	PU	1.8 V	х	х	٧	V	UART RX from host. NC if not used.
BT_AUD_IN	56	I	PD	PD	1.8 V	х	х	٧	V	Bluetooth PCM/I2S bus. Data in. NC if not used.
BT_AUD_OUT	57	0	PD	PD	1.8 V	х	х	V	V	Bluetooth PCM/I2S bus. Data out. NC if not used.
BT_AUD_FSYNC	58	I/O	PD	PD	1.8 V	х	х	V	V	Bluetooth PCM/I2S bus. Frame sync. NC if not used.
BT_AUD_CLK	60	I/O	PD	PD	1.8 V	х	х	٧	٧	Bluetooth PCM/I2S bus. NC if not used.



Table 4-1. Pin Description (continued)

PIN NAME	PIN	TYPE/	SHUTDOWN	AFTER	VOLTAGE	C	ONNEC	TIVITY	2)	DESCRIPTION
		DIR	STATE	POWER UP(1)	LEVEL	1801	1805	1831	1835	
Ground Pins	•						•		•	
GND	1, 7, 9, 15, 16, 17, 19, 20, 23, 24, 28, 29, 30, 31, 33, 34, 35, 37, 39, 44, 45, 48, 49, 54, 55, 59, 61, 63, 64, G1-G36	GND			_	V	V	V	V	

⁽¹⁾ PU = pullup; PD = pulldown.

⁽²⁾ v = connect; x = no connect.

⁽³⁾ Host must provide PU using a 10-K resistor for all non-CLK SDIO signals.

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5 Specifications

All specifications are measured at the module pins using the TI WL1835MODCOM8 evaluation board. All measurements are performed with $V_{BAT} = 3.7 \text{ V}$, $V_{IO} = 1.8 \text{ V}$, 25°C for typical values with matched RF antennas, unless otherwise indicated.

NOTE

For level-shifting I/Os with the TI WL18x5MOD, see Level Shifting WL18xx I/Os Application Report (SWRA448).

NOTE

This device as presently configured has been granted US Federal Communications Commission (FCC) equipment authorization (reference number Z64-WL18DBMOD). Any modifications to the device software or configuration, including but not limited to the init files, can cause device performance to vary beyond the scope of the currently referenced FCC authorization. Accordingly, if any user modifications are sought to be made to the device software or configuration, the user may be required to independently seek fresh FCC and other regulatory authorizations as relevant before distributing or marketing the devices or products incorporating the same.

5.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

PARAMETER	VALUE	UNIT
V _{BAT}	4.8 ⁽²⁾	V
V_{IO}	-0.5 to 2.1	V
Input voltage to analog pins	-0.5 to 2.1	V
Input voltage limits (CLK_IN)	-0.5 to VDD_IO	V
Input voltage to all other pins	-0.5 to (VDD_IO + 0.5 V)	V
Operating ambient temperature range	-20 to +70 ⁽³⁾	°C
Storage temperature, T _{stg}	-40 to +85	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

			VALUE	UNIT
V _(ESD) Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)			
	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 (2)	±250	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 Power-On Hours (POH)⁽¹⁾

OPERATING JUNCTION TEMPERATURE (°C)	РОН
125	15,000
120	20,000
115	27,000

⁽¹⁾ This information is provided solely to give the customer an estimation of the POH under certain specified conditions and does not extend the warranty for the device under TI's Standard Terms and Conditions.

^{(2) 4.8} V cumulative to 2.33 years, including charging dips and peaks

⁽³⁾ Operating free-air temperature range at which the device can operate reliably for 15K cumulative active TX power-on hours (assuming a maximum junction temperature of (T_j) of 125°C). Section 5.3, Power-On Hours (POH), describes the correlation between T_j and PoH. In the WL18xx system, a control mechanism automatically ensures T_j < 125°C. Whenever T_j approaches the threshold, this mechanism controls the transmitter patterns.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



Power-On Hours (POH)⁽¹⁾ (continued)

OPERATING JUNCTION TEMPERATURE (°C)	РОН
110	37,000
105	50,000

Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	TYP	MAX	UNIT
V _{BAT} ⁽¹⁾	DC supply range for all modes		2.9	3.7	4.8	V
V _{IO}	1.8-V I/O ring power supply voltage		1.62	1.8	1.95	V
V _{IH}	I/O high-level input voltage		0.65 x VDD_IO		VDD_IO	V
V _{IL}	I/O low-level input voltage		0		0.35 × VDD_IO	V
V _{IH_EN}	Enable inputs high-level input voltage		1.365		VDD_IO	V
V _{IL_EN}	Enable inputs low-level input voltage		0		0.4	V
V _{OH}	High-level output voltage	@ 4 mA	VDD_IO -0.45		VDD_IO	V
V _{OL}	Low-level output voltage	@ 4 mA	0		0.45	V
T_r,T_f	Input transitions time T_r, T_f from 10% to 90% (digital I/O) ⁽²⁾		1		10	ns
Tr	Output rise time from 10% to 90% (digital pins) (2)	C _L < 25 pF			5.3	ns
T _f	Output fall time from 10% to 90% (digital pins) (2)	C _L < 25 pF			4.9	ns
	Ambient operating temperature		-20		70	°C
Maximum power	WLAN operation				2.8	W
dissipation	Bluetooth operation				0.2	

^{(1) 4.8} V is applicable only for 2.33 years (30% of the time). Otherwise, maximum V_{BAT} must not exceed 4.3 V.

External Digital Slow Clock Requirements

The supported digital slow clock is 32.768 kHz digital (square wave). All core functions share a single input.

PARAMETER	CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Input slow clock frequency				32768		Hz
Input slow clock accuracy (Initial + temp + aging)	WLAN, Bluetooth				±250	ppm
Input transition time T _r ,T _f (10% to 90%)		T_r, T_f			200	ns
Frequency input duty cycle			15%	50%	85%	
Input voltage limits	Square wave, DC-	V _{IH}	0.65 x VDD_IO		VDD_IO	V_{peak}
	coupled	V _{IL}	0	(0.35 x VDD_IO	
Input impedance			1			ΜΩ
Input capacitance					5	pF

Thermal Characteristics for MOC 100-Pin Package 5.6

AIR FLOW					
NAME	DESCRIPTION	(°C/W) ⁽¹⁾			
θ_{JA}	Junction to free air ⁽²⁾	16.6			
θ_{JB}	Junction to board	6.06			
θ_{JC}	Junction to case (3)	5.13			

°C/W = degrees Celsius per watt According to the JEDEC EIA/JESD 51 document

Applies to all digital lines except PCM and slow clock lines

Modeled using the JEDEC 2s2p thermal test board with 36 thermal vias



5.7 WLAN Performance: 2.4-GHz Receiver Characteristics

over operating free-air temperature range (unless otherwise noted). All RF and performance numbers are aligned to the module pin.

PARAMETER	CONDITION	MIN	TYP	MAX	UNIT			
	RF_ANT1 pin 2.4-GHz SISO							
Operation frequency range		2412		2484	MHz			
peration requestoy range	1 Mbps DSSS		-96.3					
	2 Mbps DSSS		-93.2					
	5.5 Mbps CCK		-90.6					
	11 Mbps CCK		-87.9					
	6 Mbps OFDM		-92.0					
	9 Mbps OFDM		-90.4					
	12 Mbps OFDM		-89.5					
	18 Mbps OFDM		-87.2					
	24 Mbps OFDM		-84.1					
	36 Mbps OFDM		-80.7					
	48 Mbps OFDM		-76.5					
	54 Mbps OFDM		-74.9					
	MCS0 MM 4K		-90.4					
ensitivity: 20-MHz bandwidth. At < 10% PER limit	MCS1 MM 4K		-87.6		dBm			
	MCS2 MM 4K		-85.9					
	MCS3 MM 4K		-82.8					
	MCS4 MM 4K		-79.4					
	MCS5 MM 4K		-75.2					
	MCS6 MM 4K		-73.5					
	MCS7 MM 4K		-72.4					
	MCS0 MM 4K 40 MHz		-86.7					
	MCS7 MM 4K 40 MHz		-67.0					
	MCS0 MM 4K MRC		-92.7					
	MCS7 MM 4K MRC		-75.2					
	MCS13 MM 4K		-73.7					
	MCS14 MM 4K		-72.3					
	MCS15 MM 4K		-71.0					
	OFDM	-20.0	-10.0					
aximum input level	CCK	-10.0	-6.0		dBm			
	DSSS	-4.0	-1.0					
	2 Mbps DSSS	42.0						
djacent channel rejection: Sensitivity level +3 dB for FDM; Sensitivity level +6 dB for 11b	11 Mbps CCK	38.0			dB			
. Diff, Conditivity level to ab let 11b	54 Mbps OFDM	2.0						



WLAN Performance: 2.4-GHz Transmitter Power 5.8

over operating free-air temperature range (unless otherwise noted). All RF and performance numbers are aligned to the module pin.

PARAMETER	CONDITION ⁽¹⁾	MIN TYP	MAX	UNIT
	R	F_ANT1 Pin 2.4-GHz SIS	0	
	1 Mbps DSSS	17.3		
	2 Mbps DSSS	17.3		
	5.5 Mbps CCK	17.3		
	11 Mbps CCK	17.3		
	6 Mbps OFDM	17.1		
	9 Mbps OFDM	17.1		
	12 Mbps OFDM	17.1		
	18 Mbps OFDM	17.1		
	24 Mbps OFDM	16.2	!	
	36 Mbps OFDM	15.3	1	
	48 Mbps OFDM	14.6	i	dD.m
	54 Mbps OFDM	13.8	1	dBm
	MCS0 MM	16.1		
Dutput Power: Maximum RMS output power measured at 1 dB from IEEE spectral mask or EVM ⁽²⁾	MCS1 MM	16.1		
at 1 db Hoff feet spectral mask of EVW	MCS2 MM	16.1		
	MCS3 MM	16.1		
	MCS4 MM	15.3	1	
	MCS5 MM	14.6	i	
	MCS6 MM	13.8		
	MCS7 MM ⁽³⁾	12.6	;	
	MCS0 MM 40 MHz	14.8	1	
	MCS7 MM 40 MHz	11.3	1	
		RF_ANT1 + RF_ANT2		
	MCS12 (WL18x5)	18.5		
	MCS13 (WL18x5)	17.4		alD.ss
	MCS14 (WL18x5)	14.5	i	dBm
	MCS15 (WL18x5)	13.4		
		RF_ANT1 + RF_ANT2		
Operation frequency range		2412	2484	MHz
Return loss		-10.0		dB
Reference input impedance		50.0		Ω

- Maximum throughput (TP) degradation of up to 30% is expected, starting from 80°C ambient temperature on MIMO operation
- Regulatory constraints limit TI module output power to the following:
 - Channel 14 is used only in Japan; to keep the channel spectral shaping requirement, the power is limited:14.5 dBm.
 - Channels 1, 11 @ OFDM legacy and HT 20-MHz rates: 12 dBm

 - Channels 1, 11 @ HT 40-MHz rates: 10 dBm Channel 7 @ HT 40-MHz lower rates: 10 dBm
 - Channel 5 @ HT 40-MHz upper rates: 10 dBm
 - All 11B rates are limited to 16 dBm to comply with the ETSI PSD 10 dBm/MHz limit.
 - All OFDM rates are limited to 16.5 dBm to comply with the ETSI EIRP 20 dBm limit.
 - For clarification regarding power limitation, see the WL18xx .INI File Application Report (SWRU422).
- (3) To ensure compliance with the EVM conditions specified in the PHY chapter of IEEE Std 802.11™ 2012:
 - MCS7 20 MHz channel 12 output power is 2 dB lower than the typical value.
 - MCS7 20 MHz channel 8 output power is 1 dB lower than the typical value.



5.9 WLAN Performance: Currents

over operating free-air temperature range (unless otherwise noted). All RF and performance numbers are aligned to the module pin.

	SPECIFICATION ITEMS	TYP (AVG) – 25°C	UNITS
	Low-power mode (LPM) 2.4-GHz RX SISO20 single chain	49	
	2.4 GHz RX search SISO20	54	
	2.4-GHz RX search MIMO20	74	
	2.4-GHz RX search SISO40	59	
	2.4-GHz RX 20 M SISO 11 CCK	56	
Receiver	2.4-GHz RX 20 M SISO 6 OFDM	61	mA
	2.4-GHz RX 20 M SISO MCS7	65	
	2.4-GHz RX 20 M MRC 1 DSSS	74	
	2.4-GHz RX 20 M MRC 6 OFDM	81	
	2.4-GHz RX 20 M MRC 54 OFDM	85	
	2.4-GHz RX 40 MHz MCS7	77	
	2.4-GHz TX 20 M SISO 6 OFDM 15.4 dBm	285	
	2.4-GHz TX 20 M SISO 11 CCK 15.4 dBm	273	
Transmitter	2.4-GHz TX 20 M SISO 54 OFDM 12.7 dBm	247	A
ransmitter	2.4-GHz TX 20 M SISO MCS7 11.2 dBm	238	mA
	2.4-GHz TX 20 M MIMO MCS15 11.2 dBm	420	
	2.4-GHz TX 40 M SISO MCS7 8.2 dBm	243	

5.10 Bluetooth Performance: BR, EDR Receiver Characteristics—In-Band Signals (1)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITION	MIN	TYP	MAX	UNIT
Bluetooth BR, EDR operation frequency range		2402		2480	MHz
Bluetooth BR, EDR channel spacing			1		MHz
Bluetooth BR, EDR input impedance			50		Ω
Bluetooth BR, EDR	BR, BER = 0.1%		-92.2		
sensitivity ⁽²⁾ Dirty TX on	EDR2, BER = 0.01%		-91.7		dBm
Birty 174 on	EDR3, BER = 0.01%		-84.7		
Bluetooth EDR BER floor at	EDR2	1e-6			
sensitivity + 10 dB Dirty TX off (for 1,600,000 bits)	EDR3	1e-6			
Bluetooth BR, EDR maximum	BR, BER = 0.1%	-5.0			
usable input power	EDR2, BER = 0.1%	-15.0			dBm
	EDR3, BER = 0.1%	-15.0			
Bluetooth BR intermodulation	Level of interferers for n = 3, 4, and 5	-36.0	-30.0		dBm

⁽¹⁾ All RF and performance numbers are aligned to the module pin.

⁽²⁾ Sensitivity degradation up to -3 dB may occur due to fast clock harmonics with dirty TX on.



Bluetooth Performance: BR, EDR Receiver Characteristics—In-Band Signals⁽¹⁾ (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITION		MIN	TYP	MAX	UNIT
	BR, co-channel				10	
	EDR, co-channel	EDR2			12	
		EDR3			20	
	BR, adjacent ±1 MHz				-3.0	
D/	EDR, adjacent ±1 MHz,	EDR2			-3.0	
Bluetooth BR, EDR C/I performance	(image)	EDR3			2.0	
Numbers show wanted	BR, adjacent +2 MHz			-33.0		
signal-to-interfering-signal ratio. Smaller numbers	EDR, adjacent +2 MHz	EDR2			-33.0	dB
indicate better C/I		EDR3			-28.0	
performances (Image frequency = -1 MHz)	BR, adjacent –2 MHz				-20.0	
ricquericy = 1 Willz)	EDR, adjacent –2 MHz	EDR2			-20.0	
		EDR3			-13.0	
	BR, adjacent ≥I±3I MHz				-42.0	
	EDR, adjacent ≥I±3I MHz	EDR2			-42.0	
		EDR3			-36.0	
Bluetooth BR, EDR RF return loss				-10.0		dB

5.11 Bluetooth Performance: Transmitter, BR(1)

over operating free-air temperature range (unless otherwise noted)

over operating nee-air temperature range (unless otherwise noted)							
PARAMETER		MIN	TYP	MAX	UNIT		
DD DE output nouser(2)	V _{BAT} ≥ 3 V ⁽³⁾		11.7		dDm		
BR RF output power ⁽²⁾	V _{BAT} < 3 V ⁽³⁾		7.2		dBm		
BR gain control range			30.0		dB		
BR power control step			5.0		dB		
BR adjacent channel power M-N = 2		-43.0		dBm			
BR adjacent channel power M-N	> 2	-48.0			dBm		

- (1) All RF and performance numbers are aligned to the module pin.
- (2) Values reflect maximum power. Reduced power is available using a vendor-specific (VS) command.
- (3) VBAT is measured with an on-chip ADC that has an accuracy error of up to 5%.

5.12 Bluetooth Performance: Transmitter, EDR⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNIT
EDB output newer(2)	$V_{BAT} \ge 3 V^{(3)}$		7.2		dBm
EDR output power ⁽²⁾	$V_{BAT} < 3 V^{(3)}$		5.2		UDIII
EDR gain control range		30		dB	
EDR power control step		5		dB	
EDR adjacent channel power M-N = 1			-36		dBc
EDR adjacent channel power M-N = 2			-30		dBm
EDR adjacent channel power M-N > 2			-42		dBm

- (1) All RF and performance numbers are aligned to the module pin.
- (2) Values reflect default maximum power. Maximum power can be changed using a VS command.
- 3) VBAT is measured with an on-chip ADC that has an accuracy error of up to 5%.



5.13 Bluetooth Performance: Modulation, BR(1)

over operating free-air temperature range (unless otherwise noted)

CHARACTERISTICS	CONDITION ⁽²⁾		MIN	TYP	MAX	UNIT
BR –20 dB bandwidth				925	995	kHz
	∆f1avg	Mod data = 4 1s, 4 0s: 111100001111	145	160	170	kHz
BR modulation characteristics	∆f2max ≥ limit for at least 99.9% of all Δf2max	Mod data = 1010101	120	130		kHz
	Δf2avg, Δf1avg		85%	88%		
BR carrier frequency drift	One-slot packet		-25		25	kHz
	Three- and five-slot packet		-35		35	kHz
BR drift rate	Ifk+5 – fkl , k = 0 max				15	kHz/50 μs
BR initial carrier frequency tolerance (3)	f0-fTX		±75		±75	kHz

⁽¹⁾ All RF and performance numbers are aligned to the module pin.

5.14 Bluetooth Performance: Modulation, EDR⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

PARAMETER ⁽²⁾	CONDITION	MIN	TYP	MAX	UNIT
EDR carrier frequency stability		-5		5	kHz
EDR initial carrier frequency tolerance (3)		±75		±75	kHz
EDR RMS DEVM	EDR2		4%	15%	
	EDR3		4%	10%	
EDD 000/ DE)///	EDR2			30%	
EDR 99% DEVM	EDR3			20%	
EDR peak DEVM	EDR2		9%	25%	
	EDR3		9%	18%	

⁽¹⁾ All RF and performance numbers are aligned to the module pin.

5.15 Bluetooth LE Performance: Receiver Characteristics – In-Band Signals⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITION ⁽²⁾	MIN	TYP	MAX	UNIT
Bluetooth LE operation frequency range		2402		2480	MHz
Bluetooth LE channel spacing			2		MHz
Bluetooth LE input impedance			50		Ω
Bluetooth LE sensitivity (3) Dirty TX on			-92.2		dBm
Bluetooth LE maximum usable input power		-5			dBm
Bluetooth LE intermodulation characteristics	Level of interferers. For n = 3, 4, 5	-36	-30		dBm

⁽²⁾ Performance values reflect maximum power.

Numbers include XTAL frequency drift over temperature and aging.

⁽²⁾ Performance values reflect maximum power.

⁽³⁾ Numbers include XTAL frequency drift over temperature and aging.

⁽¹⁾ All RF and performance numbers are aligned to the module pin.

²⁾ BER of 0.1% corresponds to PER of 30.8% for a minimum of 1500 transmitted packets, according to the Bluetooth LE test specification.

⁽³⁾ Sensitivity degradation of up to -3 dB can occur due to fast clock harmonics.



Bluetooth LE Performance: Receiver Characteristics – In-Band Signals⁽¹⁾ (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITION ⁽²⁾	MIN	TYP	MAX	UNIT
Bluetooth LE C/I performance. Note: Numbers show wanted signal-to- interfering-signal ratio. Smaller numbers indicate better C/I performance. Image = -1 MHz	LE, co-channel			12	
	LE, adjacent ±1 MHz			0	
	LE, adjacent +2 MHz			-38	dB
	LE, adjacent –2 MHz			-15	
	LE, adjacent ≥ ±3 MHz			-40	

5.16 Bluetooth LE Performance: Transmitter Characteristics (1)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN TYP	MAX	UNIT
Rluetooth LE RE output nower(2)	$V_{BAT} \ge 3 V^{(3)}$	7.0		dBm
	$V_{BAT} < 3 V^{(3)}$	7.0		авш
Bluetooth LE adjacent channel power M-N = 2		-51.0		dBm
Bluetooth LE adjacent channel power M-N > 2		-54.0		dBm

- (1) All RF and performance numbers are aligned to the module pin.
- Bluetooth LE power is restricted to comply with the ETSI 10-dBm EIRP limit requirement.
- VBAT is measured with an on-chip ADC that has an accuracy error of up to 5%.

5.17 Bluetooth LE Performance: Modulation Characteristics (1)

over operating free-air temperature range (unless otherwise noted)

CHARACTERISTICS	CONDI	CONDITION ⁽²⁾		TYP	MAX	UNIT
	Δf1avg	Mod data = 4 1s, 4 0s: 111100001111	240	250	260	
Bluetooth LE modulation characteristics	Δf2max ≥ limit for at least 99.9% of all Δf2max	Mod data = 1010101	195	215		kHz
	Δf2avg, Δf1avg		85%	90%		
Bluetooth LE carrier frequency drift	If0 – fnI , n = 2,3 K	f0 – fnl , n = 2,3 K			25	kHz
Bluetooth LE drift rate	If1 – f0l and Ifn – fn-5l , n = 6,7 K				15	kHz/50 μs
Bluetooth LE initial carrier frequency tolerance (3)	fn – fTX				±75	kHz

- All RF and performance numbers are aligned to the module pin.
- Performance values reflect maximum power.
- Numbers include XTAL frequency drift over temperature and aging.

5.18 Bluetooth BR and EDR Dynamic Currents

Current is measured at output power as follows: BR at 11.7 dBm; EDR at 7.2 dBm.

USE CASE ⁽¹⁾ (2)	TYP	UNIT
BR voice HV3 + sniff	11.6	mA
EDR voice 2-EV3 no retransmission + sniff	5.9	mA
Sniff 1 attempt 1.28 s	178.0	μΑ
EDR A2DP EDR2 (master). SBC high quality – 345 kbps	10.4	mA
EDR A2DP EDR2 (master). MP3 high quality – 192 kbps	7.5	mA
Full throughput ACL RX: RX-2DH5 ⁽³⁾⁽⁴⁾	18.0	mA
Full throughput BR ACL TX: TX-DH5 ⁽⁴⁾	50.0	mA
Full throughput EDR ACL TX: TX-2DH5 ⁽⁴⁾	33.0	mA

- The role of Bluetooth in all scenarios except A2DP is slave.
- CL1P5 PA is connected to V_{BAT} , 3.7 V.
- ACL RX has the same current in all modulations.
- Full throughput assumes data transfer in one direction. (4)

Specifications



Bluetooth BR and EDR Dynamic Currents (continued)

Current is measured at output power as follows: BR at 11.7 dBm; EDR at 7.2 dBm.

USE CASE ⁽¹⁾ (2)	TYP	UNIT
Page scan or inquiry scan (scan interval is 1.28 s or 11.25 ms, respectively)	253.0	μΑ
Page scan and inquiry scan (scan interval is 1.28 s and 2.56 s, respectively)	332.0	μΑ

5.19 Bluetooth LE Currents

All current measured at output power of 7.0 dBm

USE CASE ⁽¹⁾	TYP	UNIT
Advertising, not connectable (2)	131	μΑ
Advertising, discoverable ⁽²⁾	143	μΑ
Scanning ⁽³⁾	266	μΑ
Connected, master role, 1.28-s connect interval ⁽⁴⁾	124	μΑ
Connected, slave role, 1.28-s connect interval (4)	132	μΑ

- (1) CL1p% PA is connected to V_{BAT}, 3.7 V.
- 2) Advertising in all three channels, 1.28-s advertising interval, 15 bytes advertise data
- (3) Listening to a single frequency per window, 1.28-s scan interval, 11.25-ms scan window
- (4) Zero slave connection latency, empty TX and RX LL packets

5.20 Timing and Switching Characteristics

5.20.1 Power Management

5.20.1.1 Block Diagram - Internal DC2DCs

The device incorporates three internal DC2DCs (switched-mode power supplies) to provide efficient internal supplies, derived from V_{BAT} .

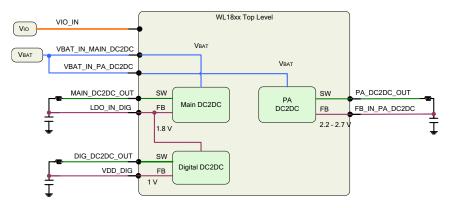


Figure 5-1. Internal DC2DCs

5.20.2 Power-Up and Shut-Down States

The correct power-up and shut-down sequences must be followed to avoid damage to the device.

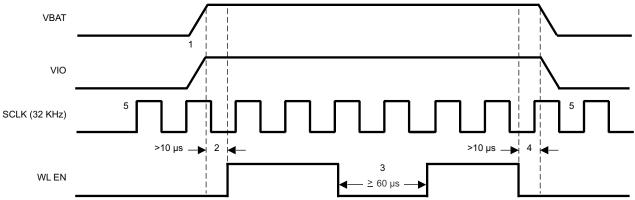
While V_{BAT} or V_{IO} or both are deasserted, no signals should be driven to the device. The only exception is the slow clock that is a fail-safe I/O.

While V_{BAT} , V_{IO} , and slow clock are fed to the device, but WL_EN is deasserted (low), the device is in SHUTDOWN state. In SHUTDOWN state all functional blocks, internal DC2DCs, clocks, and LDOs are disabled.

To perform the correct power-up sequence, assert (high) WL_EN. The internal DC2DCs, LDOs, and clock start to ramp and stabilize. Stable slow clock, V_{IO} , and V_{BAT} are prerequisites to the assertion of one of the enable signals.

To perform the correct shut-down sequence, deassert (low) WL_EN while all the supplies to the device (V_{BAT} , V_{IO} , and slow clock) are still stable and available. The supplies to the chip (V_{BAT} and V_{IO}) can be deasserted only after both enable signals are deasserted (low).

Figure 5-2 shows the general power scheme for the module, including the power-down sequence.



- NOTE: 1. Either VBAT or VIO can come up first.
 - 2. VBAT and VIO supplies and slow clock (SCLK), must be stable prior to EN being asserted and at all times when the EN is active.
 - 3. At least 60 µs is required between two successive device enables. The device is assumed to be in shutdown state during that period, meaning all enables to the device are LOW for that minimum duration.
 - 4. EN must be deasserted at least 10 µs before VBAT or VIO supply can be lowered. (Order of supply turn off after EN shutdown is immaterial)
 - 5. SCLK Fail safe I/O

Figure 5-2. Power-Up System

5.20.3 Chip Top-level Power-Up Sequence

Figure 5-3 shows the top-level power-up sequence for the chip.

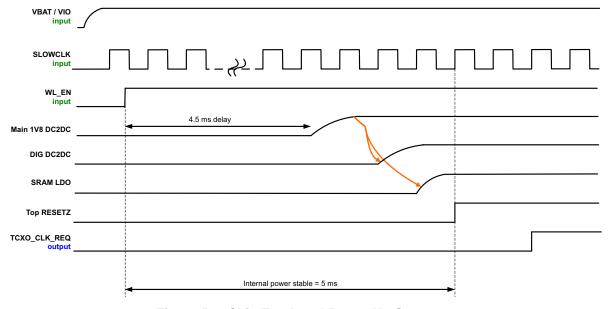


Figure 5-3. Chip Top-Level Power-Up Sequence

5.20.4 WLAN Power-Up Sequence

Figure 5-4 shows the WLAN power-up sequence.

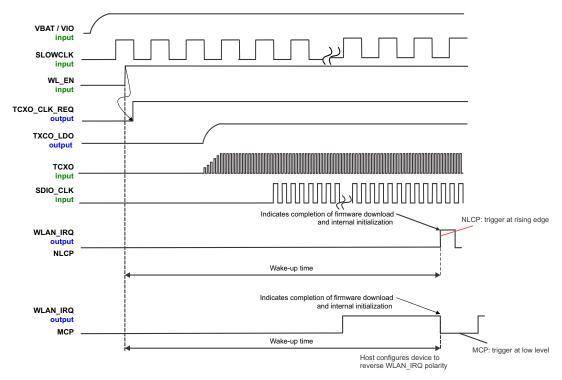


Figure 5-4. WLAN Power-Up Sequence

5.20.5 Bluetooth-Bluetooth LE Power-Up Sequence

Figure 5-5 shows the *Bluetooth-Bluetooth* LE power-up sequence.

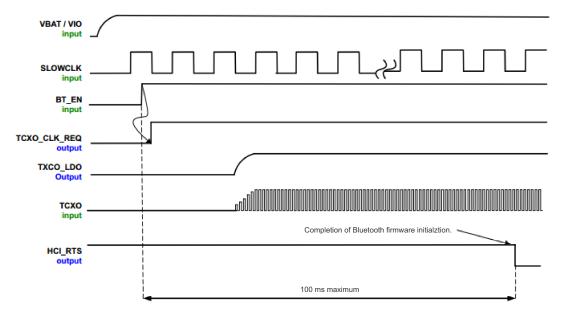


Figure 5-5. Bluetooth-Bluetooth LE Power-Up Sequence

5.20.6 WLAN SDIO Transport Layer

The SDIO is the host interface for WLAN. The interface between the host and the WL18xx module uses an SDIO interface and supports a maximum clock rate of 50 MHz.

The device SDIO also supports the following features of the SDIO V3 specification:

- 4-bit data bus
- Synchronous and asynchronous in-band interrupt
- · Default and high-speed (HS, 50 MHz) timing
- Sleep and wake commands

5.20.6.1 SDIO Timing Specifications

Figure 5-6 and Figure 5-7 show the SDIO switching characteristics over recommended operating conditions and with the default rate for input and output.

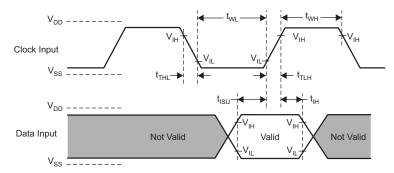


Figure 5-6. SDIO Default Input Timing

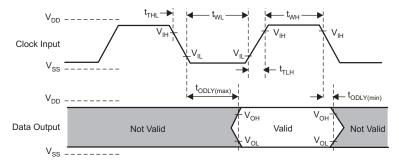


Figure 5-7. SDIO Default Output Timing

Table 5-1 lists the SDIO default timing characteristics.

Table 5-1. SDIO Default Timing Characteristics (1)

	PARAMETER ⁽²⁾	MIN	MAX	UNIT
f _{clock}	Clock frequency, CLK	0.0	26.0	MHz
DC	Low, high duty cycle	40.0%	60.0%	
t _{TLH}	Rise time, CLK		10.0	ns
t _{THL}	Fall time, CLK		10.0	ns
t_{ISU}	Setup time, input valid before CLK ↑	3.0		ns
t _{IH}	Hold time, input valid after CLK ↑	2.0		ns
t _{ODLY}	Delay time, CLK ↓ to output valid	7.0	10.0	ns
C _I	Capacitive load on outputs		15.0	pF

⁽¹⁾ To change the data out clock edge from the falling edge (default) to the rising edge, set the configuration bit.

⁽²⁾ Parameter values reflect maximum clock frequency.

5.20.6.2 SDIO Switching Characteristics – High Rate

Figure 5-8 and Figure 5-9 show the parameters for maximum clock frequency.

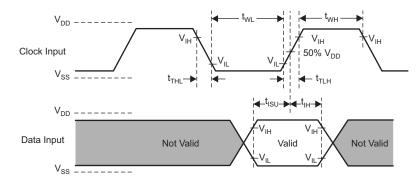


Figure 5-8. SDIO HS Input Timing

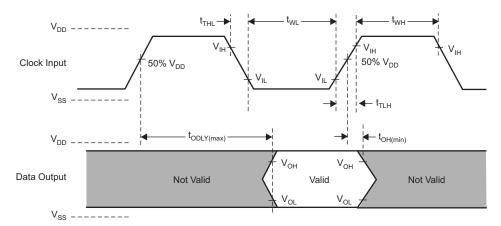


Figure 5-9. SDIO HS Output Timing

Table 5-2 lists the SDIO high-rate timing characteristics.

Table 5-2. SDIO HS Timing Characteristics

	PARAMETER	MIN	MAX	UNIT
f _{clock}	Clock frequency, CLK	0.0	52.0	MHz
DC	Low, high duty cycle	40.0%	60.0%	
t _{TLH}	Rise time, CLK		3.0	ns
t _{THL}	Fall time, CLK		3.0	ns
t _{ISU}	Setup time, input valid before CLK ↑	3.0		ns
t _{IH}	Hold time, input valid after CLK ↑	2.0		ns
t _{ODLY}	Delay time, CLK ↑ to output valid	7.0	10.0	ns
C _I	Capacitive load on outputs		10.0	pF

5.20.7 HCI UART Shared-Transport Layers for All Functional Blocks (Except WLAN)

The device incorporates a UART module dedicated to the *Bluetooth* shared-transport, host controller interface (HCI) transport layer. The HCI interface transports commands, events, and ACL between the *Bluetooth* device and its host using HCI data packets acting as a shared transport for all functional blocks except WLAN.



WLAN	SHARED HCI FOR ALL FUNCTIONAL BLOCKS EXCEPT WLAN	BLUETOOTH VOICE-AUDIO
WLAN HS SDIO	Over UART	Bluetooth PCM

The HCI UART supports most baud rates (including all PC rates) for all fast-clock frequencies up to a maximum of 4 Mbps. After power up, the baud rate is set for 115.2 Kbps, regardless of the fast-clock frequency. The baud rate can then be changed using a VS command. The device responds with a Command Complete Event (still at 115.2 Kbps), after which the baud rate change occurs.

HCI hardware includes the following features:

- Receiver detection of break, idle, framing, FIFO overflow, and parity error conditions
- Receiver-transmitter underflow detection
- CTS, RTS hardware flow control
- 4 wire (H4)

Table 5-3 lists the UART default settings.

Table 5-3. UART Default Setting

PARAMETER	VALUE
Bit rate	115.2 Kbps
Data length	8 bits
Stop-bit	1
Parity	None

5.20.7.1 UART 4-Wire Interface – H4

The interface includes four signals:

- TXD
- RXD
- CTS
- RTS

Flow control between the host and the device is byte-wise by hardware.

When the UART RX buffer of the device passes the flow-control threshold, the buffer sets the UART_RTS signal high to stop transmission from the host. When the UART_CTS signal is set high, the device stops transmitting on the interface. If HCI_CTS is set high in the middle of transmitting a byte, the device finishes transmitting the byte and stops the transmission.

Figure 5-10 shows the UART timing.



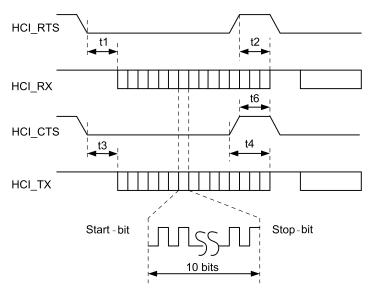


Figure 5-10. UART Timing Diagram

Table 5-4 lists the UART timing characteristics.

Table 5-4. UART Timing Characteristics

PARAMETER	CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Baud rate			37.5		4364	Kbps
Baud rate accuracy per byte	Receive-transmit		-2.5%		+1.5%	
Baud rate accuracy per bit	Receive-transmit		-12.5%		+12.5%	
CTS low to TX_DATA on		t3	0.0	2.0		μs
CTS high to TX_DATA off	Hardware flow control	t4			1.0	Byte
CTS high pulse width		t6	1.0			Bit
RTS low to RX_DATA on		t1	0.0	2.0		μs
RTS high to RX_DATA off	Interrupt set to 1/4 FIFO	t2			16.0	Bytes

Figure 5-11 shows the UART data frame.

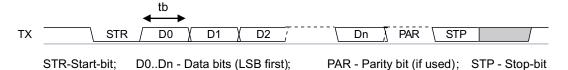


Figure 5-11. UART Data Frame

5.20.8 Bluetooth Codec-PCM (Audio) Timing Specifications

Figure 5-12 shows the Bluetooth codec-PCM (audio) timing diagram.

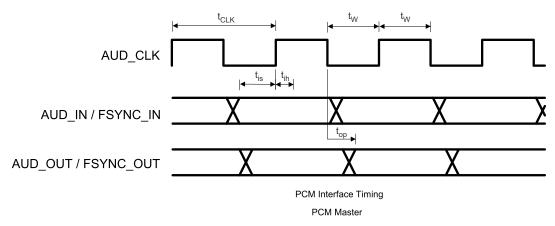


Figure 5-12. Bluetooth Codec-PCM (Audio) Master Timing Diagram

Table 5-5 lists the *Bluetooth* codec-PCM master timing characteristics.

Table 5-5. Bluetooth Codec-PCM Master Timing Characteristics

PARAMETER	SYMBOL	MIN	MAX	UNIT
Cycle time	T _{clk}	162.76 (6.144 MHz)	15625 (64 kHz)	ns
High or low pulse width	T _w	35% of T _{clk} min		
AUD_IN setup time	t _{is}	10.6		
AUD_IN hold time	t _{ih}	0		
AUD_OUT propagation time	t _{op}	0	15	
FSYNC_OUT propagation time	t _{op}	0	15	
Capacitive loading on outputs	Cı		40	pF

Table 5-6 lists the *Bluetooth* codec-PCM slave timing characteristics.

Table 5-6. Bluetooth Codec-PCM Slave Timing Characteristics

PARAMETER	SYMBOL	MIN	MAX	UNIT
Cycle time	T _{clk}	81.38 (12.288 MHz)		ns
High or low pulse width	T _w	35% of T _{clk} min		
AUD_IN setup time	t _{is}	5		
AUD_IN hold time	t _{ih}	0		
AUD_FSYNC setup time	t _{is}	5		
AUD_FSYNC hold time	t _{ih}	0		
AUD_OUT propagation time	t _{op}	0	19	
Capacitive loading on outputs	C _I		40	pF



6 Detailed Description

The WiLink 8 module is a self-contained connectivity solution based on WiLink 8 connectivity. As the eighth-generation connectivity combo chip from TI, the WiLink 8 module is based on proven technology.

Figure 6-1 shows a high-level view of the WL1835MOD variant.

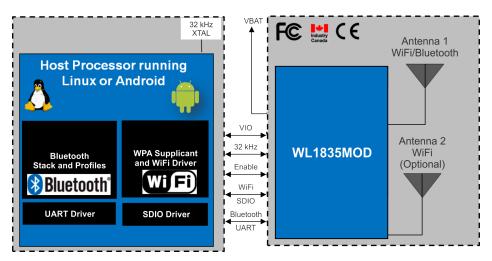


Figure 6-1. WL1835MOD High-Level System Diagram

Table 6-1 through Table 6-3 list performance parameters along with shutdown and sleep currents.

Table 6-1. WLAN Performance Parameters

WLAN ⁽¹⁾	SPECIFICATION (TYP)	CONDITIONS
Maximum TX power	17.3 dBm	1 Mbps DSSS
Minimum sensitivity	−96.3 dBm	1 Mbps DSSS
Sleep current	160 μΑ	Leakage, firmware retained
Connected IDLE	750 µA	No traffic IDLE connect
RX search	54 mA	Search (SISO20)
RX current (SISO20)	65 mA	MCS7, 2.4 GHz
TX current (SISO20)	238 mA	MCS7, 2.4 GHz, +11.2 dBm
Maximum peak current consumption during calibration (2)	850 mA	

- (1) System design power scheme must comply with both peak and average TX bursts.
- 2) Peak current V_{BAT} can hit 850 mA during device calibration.
 - . At wakeup, the WiLink 8 module performs the entire calibration sequence at the center of the 2.4-GHz band.
 - · Once a link is established, calibration is performed periodically (every 5 minutes) on the specific channel tuned.
 - The maximum VBAT value is based on peak calibration consumption with a 30% margin.

Table 6-2. Bluetooth Performance Parameters

BLUETOOTH	SPECIFICATION (TYP)	CONDITIONS
Maximum TX power	11.7 dBm	GFSK
Minimum sensitivity	−92.2 dBm	GFSK
Sniff	178 μΑ	1 attempt, 1.28 s (+4 dBm)
Page or inquiry	253 μΑ	1.28-s interrupt, 11.25-ms scan window (+4 dBm)
A2DP	7.5 mA	MP3 high quality 192 kbps (+4 dBm)



Table 6-3. Shutdown and Sleep Currents

PARAMETER	POWER SUPPLY CURRENT	TYP	UNIT	
Shutdown mode	VBAT	10		
All functions shut down	VIO	2	μΑ	
	VBAT	160	^	
WLAN sleep mode	VIO	60	μΑ	
Divisionath along mode	VBAT	110		
Bluetooth sleep mode	VIO	60	μΑ	

6.1 WLAN Features

The device supports the following WLAN features:

- Integrated 2.4-GHz power amplifiers (PAs) for a complete WLAN solution
- Baseband processor: IEEE Std 802.11b/g and IEEE Std 802.11n data rates with 20- or 40-MHz SISO and 20-MHz MIMO
- Fully calibrated system (production calibration not required)
- Medium access controller (MAC)
 - Embedded ARM[®] central processing unit (CPU)
 - Hardware-based encryption-decryption using 64-, 128-, and 256-bit WEP, TKIP, or AES keys
 - Requirements for Wi-Fi-protected access (WPA and WPA2.0) and IEEE Std 802.11i (includes hardware-accelerated Advanced Encryption Standard [AES])
- New advanced coexistence scheme with Bluetooth and Bluetooth LE wireless technology
- 2.4-GHz radio
 - Internal LNA and PA
 - IEEE Std 802.11b, 802.11g, and 802.11n
- 4-bit SDIO host interface, including high speed (HS) and V3 modes

6.2 Bluetooth Features

The device supports the following *Bluetooth* features:

- Bluetooth 4.1 as well as CSA2
- Concurrent operation and built-in coexisting and prioritization handling of Bluetooth and Bluetooth LE wireless technology, audio processing, and WLAN
- Dedicated audio processor supporting on-chip SBC encoding + A2DP
 - Assisted A2DP (A3DP): SBC encoding implemented internally
 - Assisted WB-speech (AWBS): modified SBC codec implemented internally

6.3 Bluetooth LE Features

The device supports the following *Bluetooth* LE features:

- Bluetooth 4.0 LE dual-mode standard
- All roles and role combinations, mandatory as well as optional
- Up to 10 LE connections
- Independent LE buffering allowing many multiple connections with no affect on BR-EDR performance

6.4 WiLink 8 Module Markings

Figure 6-2 shows the markings for the TI WiLink 8 module.

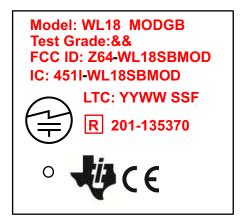


Figure 6-2. WiLink 8 Module Markings

Table 6-4 describes the WiLink 8 module markings.

Table 6-4. Description of WiLink 8 Module Markings

MARKING	DESCRIPTION
WL18 MODGB	Model
&&	Test grade (for more information, see Section 6.5, Test Grades)
Z64-WL18SBMOD	FCC ID: single modular FCC grant ID
451I-WL18SBMOD	IC: single modular IC grant ID
YYWW SSF	LTC (lot trace code): • YY = year (for example, 12 = 2012) • WW = week • SS = serial number (01 to 99) matching manufacturer lot number • F = Reserved for internal use
201-135370	R: single modular TELEC grant ID
	TELEC compliance mark
CE	CE compliance mark

6.5 Test Grades

To minimize delivery time, TI may ship the device ordered or an equivalent device currently available that contains at least the functions of the part ordered. From all aspects, this device will behave exactly the same as the part ordered. For example, if a customer orders device WL1801MOD, the part shipped can be marked with a test grade of 35, 05 (see Table 6-5).

Table 6-5. Test Grade Markings

MARK 1	WLAN	BLUETOOTH
0&	Tested	-
3&	Tested	Tested
MARK 2	WLAN 2.4 GHz	MIMO 2.4 GHz
&1	Tested	-
&5	Tested	Tested



7 Applications and Implementation

NOTE

Information in the following Applications section is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

7.1 Application Information

7.1.1 Typical Application – WL1835MODGB Reference Design

Figure 7-1 shows the TI WL1835MODGB reference design.

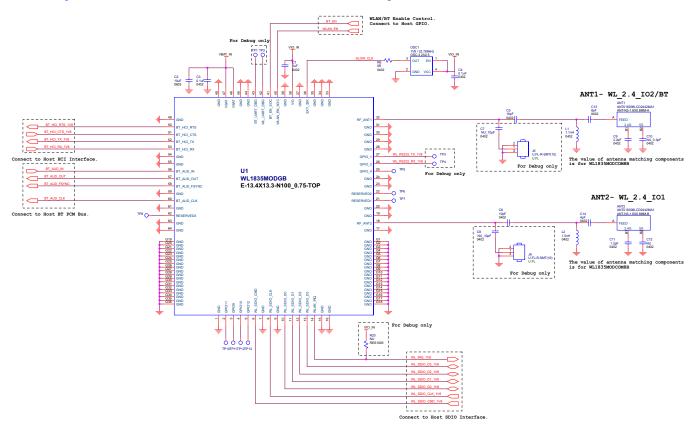


Figure 7-1. TI Module Reference Schematics

Table 7-1 lists the bill materials (BOM).

Table 7-1. BOM

ITEM	DESCRIPTION	PART NUMBER	PACKAGE	REF.	QTY	MFR
1	TI WL1835 Wi-Fi / Bluetooth module	WL1835MODGI	13.4 x 13.3 x 2.0mm	U1	1	TI
2	XOSC 3225 / 32.768 kHz / 1.8 V / ±50 ppm	7XZ3200005	3.2 x 2.5 x 1.0 mm	OSC1	1	TXC
3	Antenna / chip / 2.4 and 5 GHz / peak gain > 5 dBi	ANT016008LCD2442MA1	1.6 mm x 0.8 mm	ANT1, ANT2	2	TDK
6	Mini RF header receptacle	U.FL-R-SMT-1 (10)	3.0 x 2.6 x 1.25 mm	J5,J6	2	Hirose
7	Inductor 0402 / 1.1 nH / ±0.05 nH SMD	LQP15MN1N1W02	0402	L1	1	Murata
8	Inductor 0402 / 1.5 nH / ±0.05 nH SMD	LQP15MN1N5W02	0402	L2	1	Murata
9	Capacitor 0402 / 1.2 pF / 50 V / C0G / ±0.1 pF	GJM1555C1H1R2BB01	0402	C11	1	Murata
10	Capacitor 0402 / 2.2 pF / 50 V / C0G / ±0.1 pF	GJM1555C1H1R2BB01	0402	C9	1	Murata
11	Capacitor 0402 / 4 pF / 50 V / C0G / ±0.1 pF	GJM1555C1H4R0BB01	0402	C14	1	Murata
12	Capacitor 0402 / 8 pF / 50 V / C0G / ±0.1 pF	GJM1555C1H8R0BB01	0402	C13	1	Walsin
13	Capacitor 0402 / 10 pF / 50 V / NPO / ±5%	0402N100J500LT	0402	C5, C6	2	Walsin
14	Capacitor 0402 / 0.1 µF / 10 V / X7R / ±10%	0402B104K100CT	0402	C3, C4	1	Walsin
15	Capacitor 0402 / 1 μF / 6.3 V / X5R / ±10% / HF	GRM155R60J105KE19D	0402	C1	1	Murata
16	Capacitor 0603 / 10 µF / 6.3 V / X5R / ±20%	C1608X5R0J106M	0603	C2	1	TDK

7.1.2 Design Recommendations

This section describes the layout recommendations for the WL1835 module, RF trace, and antenna.

Table 7-2 summarizes the layout recommendations.

Table 7-2. Layout Recommendations Summary

ITEM	DESCRIPTION			
	Thermal			
1	The proximity of ground vias must be close to the pad.			
2	Signal traces must not be run underneath the module on the layer where the module is mounted.			
3	Have a complete ground pour in layer 2 for thermal dissipation.			
4	Have a solid ground plane and ground vias under the module for stable system and thermal dissipation.			
5	Increase the ground pour in the first layer and have all of the traces from the first layer on the inner layers, if possible.			
6	Signal traces can be run on a third layer under the solid ground layer, which is below the module mounting layer.			
	RF Trace and Antenna Routing			
7	The RF trace antenna feed must be as short as possible beyond the ground reference. At this point, the trace starts to radiate.			
8	The RF trace bends must be gradual with an approximate maximum bend of 45 degrees with trace mitered. RF traces must not have sharp corners.			
9	RF traces must have via stitching on the ground plane beside the RF trace on both sides.			
10	RF traces must have constant impedance (microstrip transmission line).			
11	For best results, the RF trace ground layer must be the ground layer immediately below the RF trace. The ground layer must be solid.			
12	There must be no traces or ground under the antenna section.			
13	RF traces must be as short as possible. The antenna, RF traces, and modules must be on the edge of the PCB product. The proximity of the antenna to the enclosure and the enclosure material must also be considered.			



Table 7-2. Layout Recommendations Summary (continued)

ITEM	DESCRIPTION				
	Supply and Interface				
14	The power trace for V _{BAT} must be at least 40-mil wide.				
15	The 1.8-V trace must be at least 18-mil wide.				
16	Make VBAT traces as wide as possible to ensure reduced inductance and trace resistance.				
17	If possible, shield V _{BAT} traces with ground above, below, and beside the traces.				
18	SDIO signals traces (CLK, CMD, D0, D1, D2, and D3) must be routed in parallel to each other and as short as possible (less than 12 cm). In addition, every trace length must be the same as the others. There should be enough space between traces – greater than 1.5 times the trace width or ground – to ensure signal quality, especially for the SDIO_CLK trace. Remember to keep these traces away from the other digital or analog signal traces. TI recommends adding ground shielding around these buses.				
19	SDIO and digital clock signals are a source of noise. Keep the traces of these signals as short as possible. If possible, maintain a clearance around them.				

7.1.3 RF Trace and Antenna Layout Recommendations

Figure 7-2 shows the location of the antenna on the WL1835MODCOM8B board as well as the RF trace routing from the WL1835 module (TI reference design). The Pulse multilayer antennas are mounted on the board with a specific layout and matching circuit for the radiation test conducted in FCC, CE, and IC certifications.

NOTE

For reuse of the regulatory certification, a trace of 1-dB attenuation is required on the final application board.

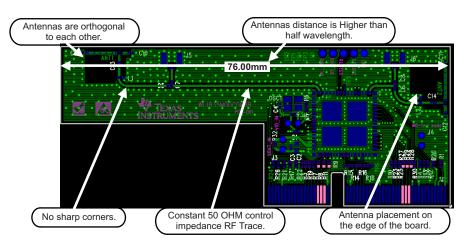


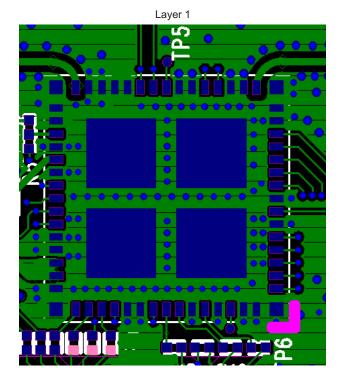
Figure 7-2. Location of Antenna and RF Trace Routing on the WL1835MODCOM8B Board

Follow these RF trace routing recommendations:

- RF traces must have 50-Ω impedance.
- RF traces must not have sharp corners.
- RF traces must have via stitching on the ground plane beside the RF trace on both sides.
- RF traces must be as short as possible. The antenna, RF traces, and module must be on the edge of the PCB product in consideration of the product enclosure material and proximity.

7.1.4 Module Layout Recommendations

Figure 7-3 shows layer 1 and layer 2 of the TI module layout.



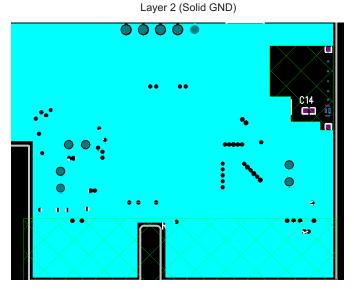


Figure 7-3. TI Module Layout

Follow these module layout recommendations:

- Ensure a solid ground plane and ground vias under the module for stable system and thermal dissipation.
- Do not run signal traces underneath the module on a layer where the module is mounted.
- Signal traces can be run on a third layer under the solid ground layer and beneath the module mounting.
- Run the host interfaces with ground on the adjacent layer to improve the return path.
- TI recommends routing the signals as short as possible to the host.

7.1.5 Thermal Board Recommendations

The TI module uses μ vias for layers 1 through 6 with full copper filling, providing heat flow all the way to the module ground pads.

TI recommends using one big ground pad under the module with vias all the way to connect the pad to all ground layers (see Figure 7-4).



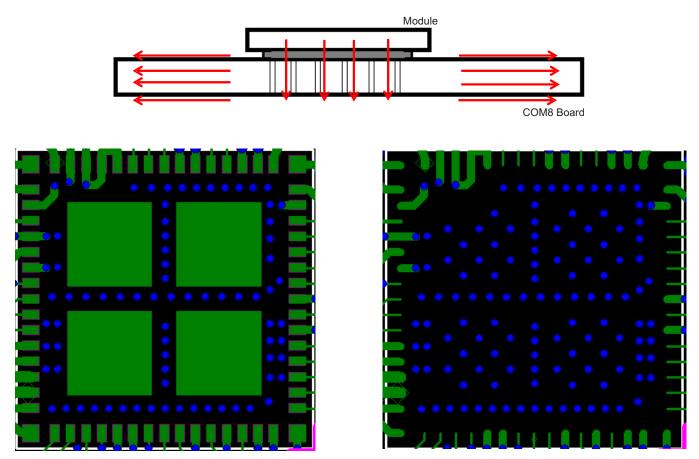


Figure 7-4. Block of Ground Pads on Bottom Side of Package

Figure 7-5 shows via array patterns, which are applied wherever possible to connect all of the layers to the TI module central or main ground pads.



Figure 7-5. Via Array Patterns

7.1.6 Baking and SMT Recommendations

7.1.6.1 Baking Recommendations

Follow these baking guidelines for the WiLink 8 module:

- Follow MSL level 3 to perform the baking process.
- After the bag is open, devices subjected to reflow solder or other high temperature processes must be mounted within 168 hours of factory conditions (< 30°C/60% RH) or stored at <10% RH.
- If the Humidity Indicator Card reads >10%, devices require baking before they are mounted.
- If baking is required, bake devices for 8 hours at 125°C.

7.1.6.2 SMT Recommendations

Figure 7-6 shows the recommended reflow profile for the WiLink 8 module.

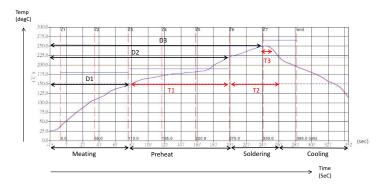


Figure 7-6. Reflow Profile for the WiLink 8 Module

Table 7-3 lists the temperature values for the profile shown in Figure 7-6.

Table 7-3. Temperature Values for Reflow Profile

ITEM	TEMPERATURE (°C)	TIME (s)	
Preheat	D1 to approximately D2: 140 to 200	T1: 80 to approximately 120	
Soldering	D2: 220	T2: 60 ±10	
Peak temperature	D3: 250 maximum	T3: 10	

NOTE

TI does not recommend the use of conformal coating or similar material on the WiLink 8 module. This coating can lead to localized stress on the WCSP solder connections inside the module and impact the device reliability. Care should be taken during module assembly process to the final PCB to avoid the presence of foreign material inside the module.



8 Device and Documentation Support

8.1 Device Support

8.1.1 Development Support

For a complete listing of development-support tools, visit the Texas Instruments WL18xx Wiki. For information on pricing and availability, contact the nearest TI field sales office or authorized distributor.

8.1.2 Device Support Nomenclature

To designate the stages in the product development cycle, TI assigns prefixes to the part numbers. These prefixes represent evolutionary stages of product development from engineering prototypes through fully qualified production devices.

- X Experimental, preproduction, sample or prototype device. Device may not meet all product qualification conditions and may not fully comply with TI specifications. Experimental/Prototype devices are shipped against the following disclaimer: "This product is still in development and is intended for internal evaluation purposes." Notwithstanding any provision to the contrary, TI makes no warranty expressed, implied, or statutory, including any implied warranty of merchantability of fitness for a specific purpose, of this device.
- null Device is qualified and released to production. TI's standard warranty applies to production devices.

8.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 8-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
WL1801MOD	Click here	Click here	Click here	Click here	Click here
WL1805MOD	Click here	Click here	Click here	Click here	Click here
WL1831MOD	Click here	Click here	Click here	Click here	Click here
WL1835MOD	Click here	Click here	Click here	Click here	Click here

8.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

- TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.
- TI Embedded Processors Wiki Texas Instruments Embedded Processors Wiki. Established to help developers get started with Embedded Processors from Texas Instruments and to foster innovation and growth of general knowledge about the hardware and software surrounding these devices.

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Android is a trademark of Google, Inc.

IEEE Std 802.11 is a trademark of IEEE.

Linux is a registered trademark of Linus Torvalds.

Wi-Fi is a registered trademark of Wi-Fi Alliance.

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8.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.



9 Mechanical Packaging and Orderable Information

9.1 TI Module Mechanical Outline

Figure 9-1 shows the mechanical outline for the device.

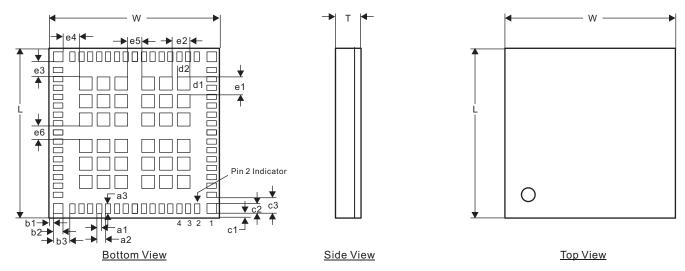


Figure 9-1. TI Module Mechanical Outline

Table 9-1 lists the dimensions for the mechanical outline of the device.

NOTE

The TI module weighs 0.684 g (±0.005 g).

Table 9-1. Dimensions for TI Module Mechanical Outline

MARKING	MIN (mm)	NOM (mm)	MAX (mm)	MARKING	MIN (mm)	NOM (mm)	MAX (mm)
L (body size)	13.20	13.30	13.40	c2	0.65	0.75	0.85
W (body size)	13.30	13.40	13.50	c3	1.15	1.25	1.35
T (thickness)	1.90		2.00	d1	0.90	1.00	1.10
a1	0.30	0.40	0.50	d2	0.90	1.00	1.10
a2	0.60	0.70	0.80	e1	1.30	1.40	1.50
a3	0.65	0.75	0.85	e2	1.30	1.40	1.50
b1	0.20	0.30	0.40	e3	1.15	1.25	1.35
b2	0.65	0.75	0.85	e4	1.20	1.30	1.40
b3	1.20	1.30	1.40	e5	1.00	1.10	1.20
c1	0.20	0.30	0.40	e6	1.00	1.10	1.20

Product Folder Links: WL1801MOD WL1805MOD WL1831MOD WL1835MOD

9.2 Tape and Reel Information

Emboss taping specification for MOC 100 pin.

9.2.1 Tape and Reel Specification

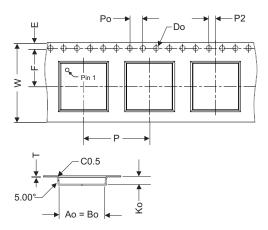


Figure 9-2. Tape Specification

Table 9-2. Dimensions for Tape Specification

ITEM	w	E	F	Р	Ро	P2	Do	Т	Ao	Во	Ko
DIMENSION	24.00	1.75	11.50	20.00	4.00	2.00	2.00	0.35	13.80	13.80	2.50
(mm)	(±0.30)	(±0.10)	(±0.10)	(±0.10)	(±0.10)	(±0.10)	(±0.10)	(±0.05)	(±0.10)	(±0.10)	(±0.10)

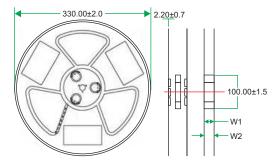


Figure 9-3. Reel Specification

Table 9-3. Dimensions for Reel Specification

ITEM	W1	W2		
DIMENSION (mm)	24.4 (+1.5, -0.5)	30.4 (maximum)		

9.2.2 Packing Specification

9.2.2.1 Reel Box

The reel is packed in a moisture barrier bag fastened by heat-sealing. Each moisture-barrier bag is packed into a reel box, as shown in Figure 9-4.

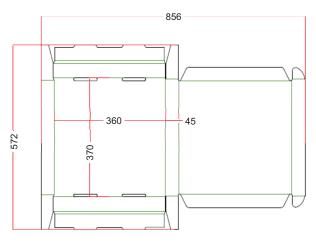


Figure 9-4. Reel Box

The reel box is made of corrugated fiberboard.

9.2.2.2 Shipping Box

Figure 9-5 shows a typical shipping box. If the shipping box has excess space, filler (such as cushion) is added.

NOTE

The size of the shipping box may vary depending on the number of reel boxes packed.

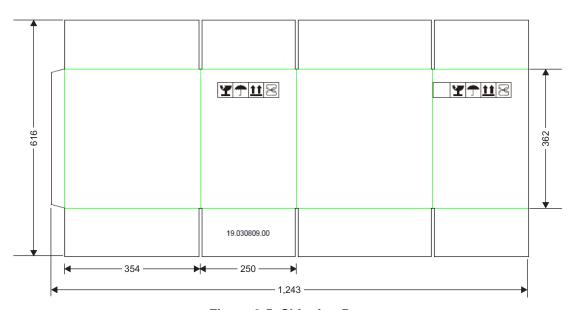


Figure 9-5. Shipping Box

The shipping box is made of corrugated fiberboard.

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9.3 Packaging Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGE OPTION ADDENDUM

Orderable Device	Status(1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan(2)	Lead/Ball Finish	MSL Peak Temp (°C) (3)	Op Temp (°C)
WL1801MODGBMOCR	ACTIVE	Module	MOC	100	1200	RoHS Compliant	NiPdAu	250	-20 to 70
WL1801MODGBMOCT	ACTIVE	Module	MOC	100	250	RoHS Compliant	NiPdAu	250	-20 to 70
WL1805MODGBMOCR	ACTIVE	Module	MOC	100	1200	RoHS Compliant	NiPdAu	250	-20 to 70
WL1805MODGBMOCT	ACTIVE	Module	MOC	100	250	RoHS Compliant	NiPdAu	250	-20 to 70
WL1831MODGBMOCR	ACTIVE	Module	MOC	100	1200	RoHS Compliant	NiPdAu	250	-20 to 70
WL1831MODGBMOCT	ACTIVE	Module	MOC	100	250	RoHS Compliant	NiPdAu	250	-20 to 70
WL1835MODGBMOCR	ACTIVE	Module	MOC	100	1200	RoHS Compliant	NiPdAu	250	-20 to 70
WL1835MODGBMOCT	ACTIVE	Module	MOC	100	250	RoHS Compliant	NiPdAu	250	-20 to 70

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PRE_PROD Unannounced device, not in production, not available for mass market, nor on the web, samples not available.

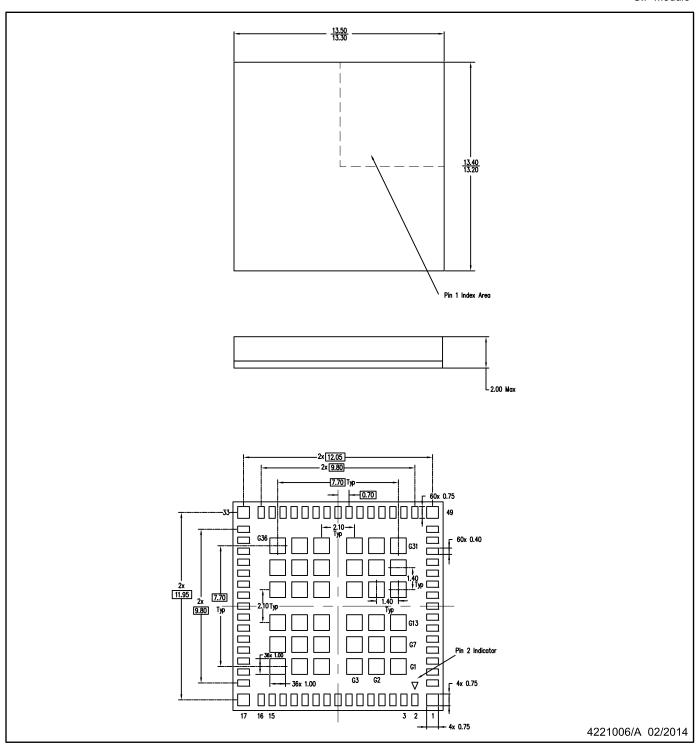
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

- (2) RoHS Compliance: This product has an RoHS exemption for one or more subcomponent(s). The product is otherwise considered Pb-Free (RoHS compatible) as defined above.
- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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SIP Module

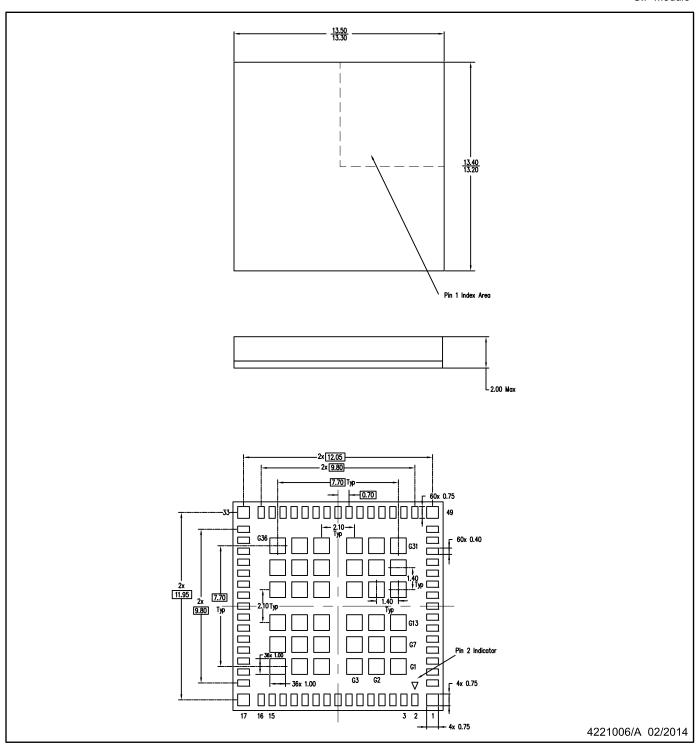


NOTES:

- All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



SIP Module



NOTES:

- All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



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